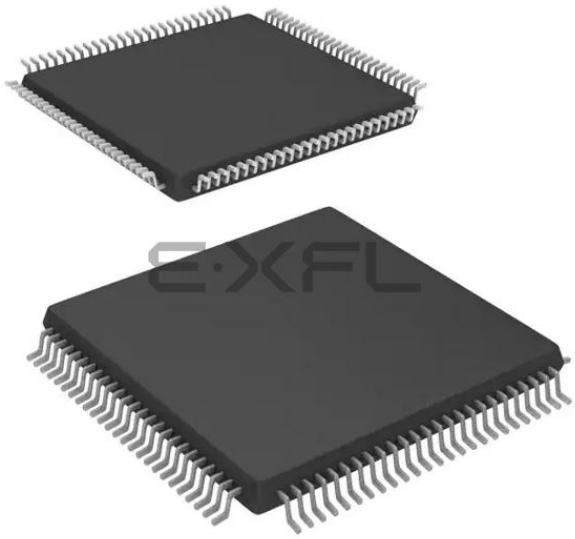

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	36864
Number of I/O	71
Number of Gates	125000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	100-TQFP
Supplier Device Package	100-VQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3pn125-vq100i

***Table 3-3* • Quadrant Global Pin Name (continued)**

Differential I/O Pairs	GAAO/IOuxwByVz GAA1/IOuxwByVz	The output of the different pair will drive the global.
	GABO/IOuxwByVz GAB1/IOuxwByVz	The output of the different pair will drive the global.
	GACO/IOuxwByVz GAC1/IOuxwByVz	The output of the different pair will drive the global.
	GBAO/IOuxwByVz GBA1/IOuxwByVz	The output of the different pair will drive the global.
	GBBO/IOuxwByVz GBB1/IOuxwByVz	The output of the different pair will drive the global.
	GBCO/IOuxwByVz GBC1/IOuxwByVz	The output of the different pair will drive the global.
	GDAO/IOuxwByVz GDA1/IOuxwByVz	The output of the different pair will drive the global.
	GDBO/IOuxwByVz GDB1/IOuxwByVz	The output of the different pair will drive the global.
	GDCO/IOuxwByVz GDC1/IOuxwByVz	The output of the different pair will drive the global.
	GEAO/IOuxwByVz GEA1/IOuxwByVz	The output of the different pair will drive the global.
	GEBO/IOuxwByVz GEB1/IOuxwByVz	The output of the different pair will drive the global.
	GECO/IOuxwByVz GEC1/IOuxwByVz	The output of the different pair will drive the global.

Note: Only one of the I/Os can be directly connected to a quadrant at a time.

Unused Global I/O Configuration

The unused clock inputs behave similarly to the unused Pro I/Os. The Microsemi Designer software automatically configures the unused global pins as inputs with pull-up resistors if they are not used as regular I/O.

I/O Banks and Global I/O Standards

In low power flash devices, any I/O or internal logic can be used to drive the global network. However, only the global macro placed at the global pins will use the hardwired connection between the I/O and global network. Global signal (signal driving a global macro) assignment to I/O banks is no different from regular I/O assignment to I/O banks with the exception that you are limited to the pin placement location available. Only global signals compatible with both the VCCI and VREF standards can be assigned to the same bank.

***Table 3-5* • Globals/Spines/Rows for IGLOO PLUS Devices**

IGLOO PLUS Devices	Chip Globals	Quadrant Globals (4×3)	Clock Trees	Globals/ Spines per Tree	Total Spines per Device	VersaTiles in Each Tree	Total VersaTiles	Rows in Each Spine
AGLP030	6	0	2	9	18	384*	792	12
AGLP060	6	12	4	9	36	384*	1,584	12
AGLP125	6	12	8	9	72	384*	3,120	12

*Note: *Clock trees that are located at far left and far right will support more VersaTiles.*

***Table 3-6* • Globals/Spines/Rows for Fusion Devices**

Fusion Device	Chip Globals	Quadrant Globals (4×3)	Clock Trees	Globals/ Spines per Tree	Total Spines per Device	VersaTiles in Each Tree	Total VersaTiles	Rows in Each Spine
AFS090	6	12	6	9	54	384	2,304	12
AFS250	6	12	8	9	72	768	6,144	24
AFS600	6	12	12	9	108	1,152	13,824	36
AFS1500	6	12	20	9	180	1,920	38,400	60

Implementing EXTFB in ProASIC3/E Devices

When the external feedback (EXTFB) signal of the PLL in the ProASIC3/E devices is implemented, the phase detector of the PLL core receives the reference clock (CLKA) and EXTFB as inputs. EXTFB must be sourced as an INBUF macro and located at the global/chip clock location associated with the target PLL by Designer software. EXTFB cannot be sourced from the FPGA fabric.

The following example shows CLKA and EXTFB signals assigned to two global I/Os in the same global area of ProASIC3E device.

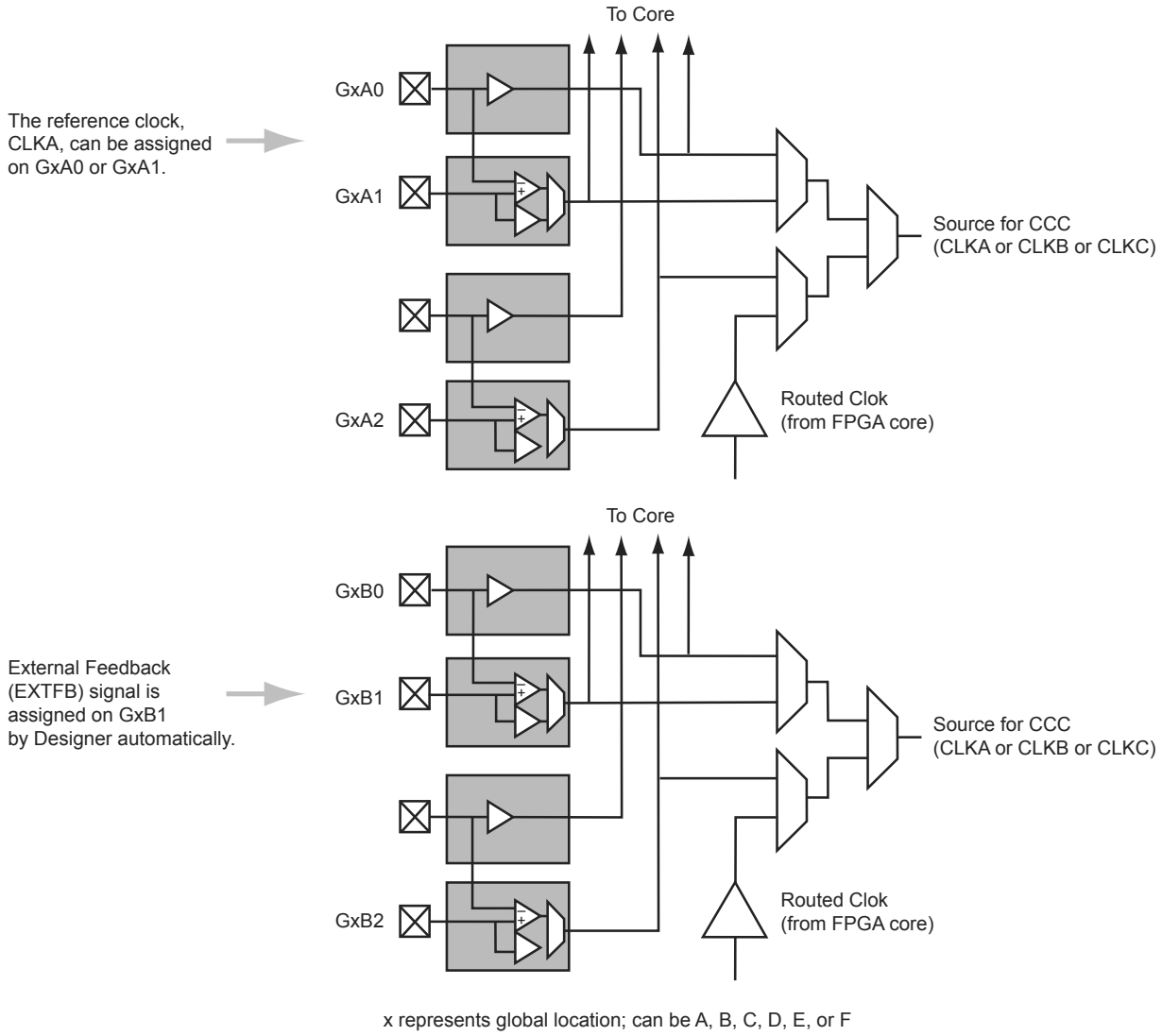


Figure 4-5 • **CLKA and EXTFB Assigned to Global I/Os**

```
  wire VCC, GND;

  VCC VCC_1_net(.Y(VCC));
  GND GND_1_net(.Y(GND));
  CLKDLY Inst1(.CLK(CLK), .GL(GL), .DLYGL0(VCC), .DLYGL1(GND), .DLYGL2(VCC),
    .DLYGL3(GND), .DLYGL4(GND));

endmodule
```

Detailed Usage Information

Clock Frequency Synthesis

Deriving clocks of various frequencies from a single reference clock is known as frequency synthesis. The PLL has an input frequency range from 1.5 to 350 MHz. This frequency is automatically divided down to a range between 1.5 MHz and 5.5 MHz by input dividers (not shown in Figure 4-19 on page 84) between PLL macro inputs and PLL phase detector inputs. The VCO output is capable of an output range from 24 to 350 MHz. With dividers before the input to the PLL core and following the VCO outputs, the VCO output frequency can be divided to provide the final frequency range from 0.75 to 350 MHz. Using SmartGen, the dividers are automatically set to achieve the closest possible matches to the specified output frequencies.

Users should be cautious when selecting the desired PLL input and output frequencies and the I/O buffer standard used to connect to the PLL input and output clocks. Depending on the I/O standards used for the PLL input and output clocks, the I/O frequencies have different maximum limits. Refer to the family datasheets for specifications of maximum I/O frequencies for supported I/O standards. Desired PLL input or output frequencies will not be achieved if the selected frequencies are higher than the maximum I/O frequencies allowed by the selected I/O standards. Users should be careful when selecting the I/O standards used for PLL input and output clocks. Performing post-layout simulation can help detect this type of error, which will be identified with pulse width violation errors. Users are strongly encouraged to perform post-layout simulation to ensure the I/O standard used can provide the desired PLL input or output frequencies. Users can also choose to cascade PLLs together to achieve the high frequencies needed for their applications. Details of cascading PLLs are discussed in the "Cascading CCCs" section on page 109.

In SmartGen, the actual generated frequency (under typical operating conditions) will be displayed beside the requested output frequency value. This provides the ability to determine the exact frequency that can be generated by SmartGen, in real time. The log file generated by SmartGen is a useful tool in determining how closely the requested clock frequencies match the user specifications. For example, assume a user specifies 101 MHz as one of the secondary output frequencies. If the best output frequency that could be achieved were 100 MHz, the log file generated by SmartGen would indicate the actual generated frequency.

Simulation Verification

The integration of the generated PLL and CLKDLY modules is similar to any VHDL component or Verilog module instantiation in a larger design; i.e., there is no special requirement that users need to take into account to successfully synthesize their designs.

For simulation purposes, users need to refer to the VITAL or Verilog library that includes the functional description and associated timing parameters. Refer to the Software Tools section of the Microsemi SoC Products Group website to obtain the family simulation libraries. If Designer is installed, these libraries are stored in the following locations:

<Designer_Installation_Directory>\lib\vtl\95\proasic3.vhd

<Designer_Installation_Directory>\lib\vtl\95\proasic3e.vhd

<Designer_Installation_Directory>\lib\vlog\proasic3.v

<Designer_Installation_Directory>\lib\vlog\proasic3e.v

For Libero users, there is no need to compile the simulation libraries, as they are conveniently pre-compiled in the Model*Sim*® Microsemi simulation tool.

The following is an example of a PLL configuration utilizing the clock frequency synthesis and clock delay adjustment features. The steps include generating the PLL core with SmartGen, performing simulation for verification with Model*Sim*, and performing static timing analysis with SmartTime in Designer.

Parameters of the example PLL configuration:

Input Frequency – 20 MHz

Primary Output Requirement – 20 MHz with clock advancement of 3.02 ns

Secondary 1 Output Requirement – 40 MHz with clock delay of 2.515 ns

Figure 4-29 shows the SmartGen settings. Notice that the overall delays are calculated automatically, allowing the user to adjust the delay elements appropriately to obtain the desired delays.

***Figure 4-29* • SmartGen Settings**

After confirming the correct settings, generate a structural netlist of the PLL and verify PLL core settings by checking the log file:

```
Name                          : test_pll_delays
Family                        : ProASIC3E
Output Format                 : VHDL
Type                          : Static PLL
Input Freq(MHz)               : 20.000
CLKA Source                   : Hardwired I/O
Feedback Delay Value Index    : 21
Feedback Mux Select           : 2
XDLY Mux Select               : No
Primary Freq(MHz)             : 20.000
Primary PhaseShift            : 0
Primary Delay Value Index     : 1
Primary Mux Select            : 4
Secondary1 Freq(MHz)          : 40.000
Use GLB                       : YES
Use YB                        : NO
…
…
…
Primary Clock frequency 20.000
Primary Clock Phase Shift 0.000
```

```
Primary Clock Output Delay from CLKA -3.020

Secondary1 Clock frequency 40.000
Secondary1 Clock Phase Shift 0.000
Secondary1 Clock Global Output Delay from CLKA 2.515
```

Next, perform simulation in Model*Sim* to verify the correct delays. Figure 4-30 shows the simulation results. The delay values match those reported in the SmartGen PLL Wizard.

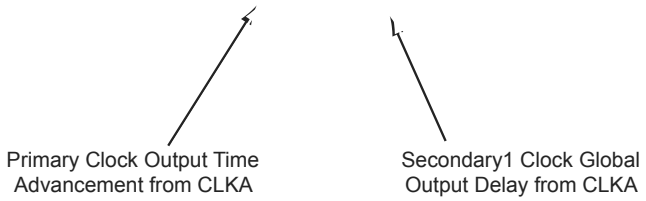
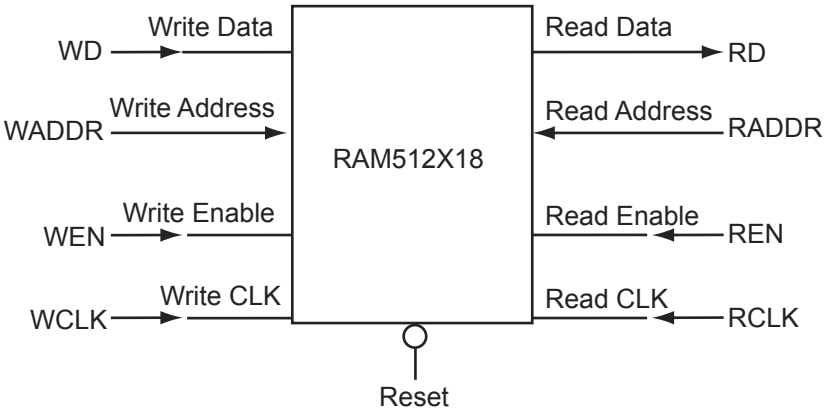


Figure 4-30 • **Model*Sim* Simulation Results**

The timing can also be analyzed using SmartTime in Designer. The user should import the synthesized netlist to Designer, perform Compile and Layout, and then invoke SmartTime. Go to **Tools** > **Options** and change the maximum delay operating conditions to **Typical Case**. Then expand the Clock-to-Out paths of GLA and GLB and the individual components of the path delays are shown. The path of GLA is shown in Figure 4-31 on page 107 displaying the same delay value.



Note: For timing diagrams of the RAM signals, refer to the appropriate family datasheet.

***Figure 6-5* • 512X18 Two-Port RAM Block Diagram**

Signal Descriptions for RAM512X18

RAM512X18 has slightly different behavior from RAM4K9, as it has dedicated read and write ports.

WW and RW

These signals enable the RAM to be configured in one of the two allowable aspect ratios (Table 6-5).

***Table 6-5* • Aspect Ratio Settings for WW[1:0]**

WW[1:0]	RW[1:0]	D×W
01	01	512×9
10	10	256×18
00, 11	00, 11	Reserved

WD and RD

These are the input and output data signals, and they are 18 bits wide. When a 512×9 aspect ratio is used for write, WD[17:9] are unused and must be grounded. If this aspect ratio is used for read, RD[17:9] are undefined.

WADDR and RADDR

These are read and write addresses, and they are nine bits wide. When the 256×18 aspect ratio is used for write or read, WADDR[8] and RADDR[8] are unused and must be grounded.

WCLK and RCLK

These signals are the write and read clocks, respectively. They can be clocked on the rising or falling edge of WCLK and RCLK.

WEN and REN

These signals are the write and read enables, respectively. They are both active-low by default. These signals can be configured as active-high.

RESET

This active-low signal resets the control logic, forces the output hold state registers to zero, disables reads and writes from the SRAM block, and clears the data hold registers when asserted. It does not reset the contents of the memory array.

While the RESET signal is active, read and write operations are disabled. As with any asynchronous reset signal, care must be taken not to assert it too close to the edges of active read and write clocks.

PIPE

This signal is used to specify pipelined read on the output. A LOW on PIPE indicates a nonpipelined read, and the data appears on the output in the same clock cycle. A HIGH indicates a pipelined read, and data appears on the output in the next clock cycle.

Cold-Sparing Support

Cold-sparing refers to the ability of a device to leave system data undisturbed when the system is powered up, while the component itself is powered down, or when power supplies are floating.

Cold-sparing is supported on all IGLOO nano and ProASIC3 nano devices only when the user provides resistors from each power supply to ground. The resistor value is calculated based on the decoupling capacitance on a given power supply. The RC constant should be greater than 3 µs.

To remove resistor current during operation, it is suggested that the resistor be disconnected (e.g., with an NMOS switch) from the power supply after the supply has reached its final value. Refer to the "Power-Up/-Down Behavior of Low Power Flash Devices" section on page 307 for details on cold-sparing.

Cold-sparing means that a subsystem with no power applied (usually a circuit board) is electrically connected to the system that is in operation. This means that all input buffers of the subsystem must present very high input impedance with no power applied so as not to disturb the operating portion of the system.

When targeting low power applications, I/O cold-sparing may add additional current if a pin is configured with either a pull-up or pull-down resistor and driven in the opposite direction. A small static current is induced on each I/O pin when the pin is driven to a voltage opposite to the weak pull resistor. The current is equal to the voltage drop across the input pin divided by the pull resistor. Refer to the "Detailed I/O DC Characteristics" section of the appropriate family datasheet for the specific pull resistor value for the corresponding I/O standard.

For example, assuming an LVTTL 3.3 V input pin is configured with a weak pull-up resistor, a current will flow through the pull-up resistor if the input pin is driven LOW. For LVTTL 3.3 V, the pull-up resistor is ~45 kΩ, and the resulting current is equal to 3.3 V / 45 kΩ = 73 µA when the I/O pin is driven LOW. This is true also when a weak pull-down is chosen and the input pin is driven HIGH. This current can be avoided by driving the input Low when a weak pull-down resistor is used and driving it HIGH when a weak pull-up resistor is used.

This current draw can occur in the following cases:

- In Active and Static modes:
  - Input buffers with pull-up, driven Low
  - Input buffers with pull-down, driven High
  - Bidirectional buffers with pull-up, driven Low
  - Bidirectional buffers with pull-down, driven High
  - Output buffers with pull-up, driven Low
  - Output buffers with pull-down, driven High
  - Tristate buffers with pull-up, driven Low
  - Tristate buffers with pull-down, driven High
- In Flash*Freeze mode (not supported on ProASIC3 nano devices):
  - Input buffers with pull-up, driven Low
  - Input buffers with pull-down, driven High
  - Bidirectional buffers with pull-up, driven Low
  - Bidirectional buffers with pull-down, driven High

Electrostatic Discharge Protection

Low power flash devices are tested per JEDEC Standard JESD22-A114-B.

These devices contain clamp diodes at every I/O, global, and power pad. Clamp diodes protect all device pads against damage from ESD as well as from excessive voltage transients.

All nano devices are qualified to the Human Body Model (HBM) and the Charged Device Model (CDM).

***Table 7-12* • I/O Hot-Swap and 5 V Input Tolerance Capabilities in nano Devices**

I/O Assignment	Clamp Diode	Hot Insertion	5 V Input Tolerance	Input Buffer	Output Buffer
3.3 V LVTTL/LVCMOS	No	Yes	Yes*	Enabled/Disabled	
LVCMOS 2.5 V	No	Yes	No	Enabled/Disabled	
LVCMOS 1.8 V	No	Yes	No	Enabled/Disabled	
LVCMOS 1.5 V	No	Yes	No	Enabled/Disabled	
LVCMOS 1.2 V	No	Yes	No	Enabled/Disabled	

** Can be implemented with an external IDT bus switch, resistor divider, or Zener with resistor.*

5 V Input and Output Tolerance

nano devices can be made 5 V–input–tolerant for certain I/O standards by using external level shifting techniques. 5 V output compliance can be achieved using certain I/O standards.

Table 7-5 on page 163 shows the I/O standards that support 5 V input tolerance. Only 3.3 V LVTTL/LVCMOS standards support 5 V output tolerance.

5 V Input Tolerance

I/Os can support 5 V input tolerance when LVTTL 3.3 V or LVCMOS 3.3 V configurations are used (see Table 7-12). There are three recommended solutions for achieving 5 V receiver tolerance (see Figure 7-5 on page 172 to Figure 7-7 on page 173 for details of board and macro setups). All the solutions meet a common requirement of limiting the voltage at the input to 3.6 V or less. In fact, the I/O absolute maximum voltage rating is 3.6 V, and any voltage above 3.6 V may cause long-term gate oxide failures.

Solution 1

The board-level design must ensure that the reflected waveform at the pad does not exceed the limits provided in the recommended operating conditions in the datasheet. This is a requirement to ensure long-term reliability.

This solution requires two board resistors, as demonstrated in Figure 7-5 on page 172. Here are some examples of possible resistor values (based on a simplified simulation model with no line effects and 10 Ω transmitter output resistance, where Rtx_out_high = (VCCI – VOH) / I_{OH} and Rtx_out_low = VOL / I_{OL}).

Example 1 (high speed, high current):

Rtx_out_high = Rtx_out_low = 10 Ω

R1 = 36 Ω (±5%), P(r1)min = 0.069 Ω

R2 = 82 Ω (±5%), P(r2)min = 0.158 Ω

Imax_tx = 5.5 V / (82 × 0.95 + 36 × 0.95 + 10) = 45.04 mA

t_{RISE} = t_{FALL} = 0.85 ns at C_pad_load = 10 pF (includes up to 25% safety margin)

t_{RISE} = t_{FALL} = 4 ns at C_pad_load = 50 pF (includes up to 25% safety margin)

***Table 7-13* • Comparison Table for 5 V–Compliant Receiver Solutions**

Solution	Board Components	Speed	Current Limitations
1	Two resistors	Low to High[1]	Limited by transmitter's drive strength
2	Resistor and Zener 3.3 V	Medium	Limited by transmitter's drive strength
3	Bus switch	High	N/A

Notes:

1. *Speed and current consumption increase as the board resistance values decrease.*
2. *Resistor values ensure I/O diode long-term reliability.*
3. *At 70°C, customers could still use 420 Ω on every I/O.*
4. *At 85°C, a 5 V solution on every other I/O is permitted, since the resistance is lower (150 Ω) and the current is higher. Also, the designer can still use 420 Ω and use the solution on every I/O.*
5. *At 100°C, the 5 V solution on every I/O is permitted, since 420 Ω are used to limit the current to 5.9 mA.*

5 V Output Tolerance

nano Standard I/Os must be set to 3.3 V LVTTL or 3.3 V LVCMOS mode to reliably drive 5 V TTL receivers. It is also critical that there be NO external I/O pull-up resistor to 5 V, since this resistor would pull the I/O pad voltage beyond the 3.6 V absolute maximum value and consequently cause damage to the I/O.

When set to 3.3 V LVTTL or 3.3 V LVCMOS mode, the I/Os can directly drive signals into 5 V TTL receivers. In fact, V_{OL} = 0.4 V and V_{OH} = 2.4 V in both 3.3 V LVTTL and 3.3 V LVCMOS modes exceeds the V_{IL} = 0.8 V and V_{IH} = 2 V level requirements of 5 V TTL receivers. Therefore, level 1 and level 0 will be recognized correctly by 5 V TTL receivers.

Schmitt Trigger

A Schmitt trigger is a buffer used to convert a slow or noisy input signal into a clean one before passing it to the FPGA. Using Schmitt trigger buffers guarantees a fast, noise-free input signal to the FPGA.

nano devices have Schmitt triggers built into their I/O circuitry. Schmitt Trigger is available on all I/O configurations.

This feature can be implemented by using a Physical Design Constraints (PDC) command (Table 7-5 on page 163) or by selecting a check box in the I/O Attribute Editor in Designer. The check box is cleared by default.

I/O Register Combining

Every I/O has several embedded registers in the I/O tile that are close to the I/O pads. Rather than using the internal register from the core, the user has the option of using these registers for faster clock-to-out timing, and external hold and setup. When combining these registers at the I/O buffer, some architectural rules must be met. Provided these rules are met, the user can enable register combining globally during Compile (as shown in the "Compiling the Design" section in the "I/O Software Control in Low Power Flash Devices" section on page 185.

This feature is supported by all I/O standards.

Rules for Registered I/O Function:

1. The fanout between an I/O pin (D, Y, or E) and a register must be equal to one for combining to be considered on that pin.
2. All registers (Input, Output, and Output Enable) connected to an I/O must share the same clear or preset function:
   – If one of the registers has a CLR pin, all the other registers that are candidates for combining in the I/O must have a CLR pin.

I/O Cell Architecture

Low power flash devices support DDR in the I/O cells in four different modes: Input, Output, Tristate, and Bidirectional pins. For each mode, different I/O standards are supported, with most I/O standards having special sub-options. For the ProASIC3 nano and IGLOO nano devices, DDR is supported only in the 60 k, 125 k, and 250 k logic densities. Refer to Table 9-2 for a sample of the available I/O options. Additional I/O options can be found in the relevant family datasheet.

***Table 9-2* • DDR I/O Options**

DDR Register Type	I/O Type	I/O Standard	Sub-Options	Comments
Receive Register	Input	Normal	None	3.3 V TTL (default)
		LVCMOS	Voltage	1.5 V, 1.8 V, 2.5 V, 5 V (1.5 V default)
			Pull-Up	None (default)
		PCI/PCI-X	None	
		GTL/GTL+	Voltage	2.5 V, 3.3 V (3.3 V default)
		HSTL	Class	I / II (I default)
		SSTL2/SSTL3	Class	I / II (I default)
		LVPECL	None	
		LVDS	None	
Transmit Register	Output	Normal	None	3.3 V TTL (default)
		LVTTL	Output Drive	2, 4, 6, 8, 12, 16, 24, 36 mA (8 mA default)
			Slew Rate	Low/high (high default)
		LVCMOS	Voltage	1.5 V, 1.8 V, 2.5 V, 5 V (1.5 V default)
		PCI/PCI-X	None	
		GTL/GTL+	Voltage	1.8 V, 2.5 V, 3.3 V (3.3 V default)
		HSTL	Class	I / II (I default)
		SSTL2/SSTL3	Class	I / II (I default)
		LVPECL*	None	
		LVDS*	None	

*Note: *IGLOO nano and ProASIC3 nano devices do not support differential inputs.*

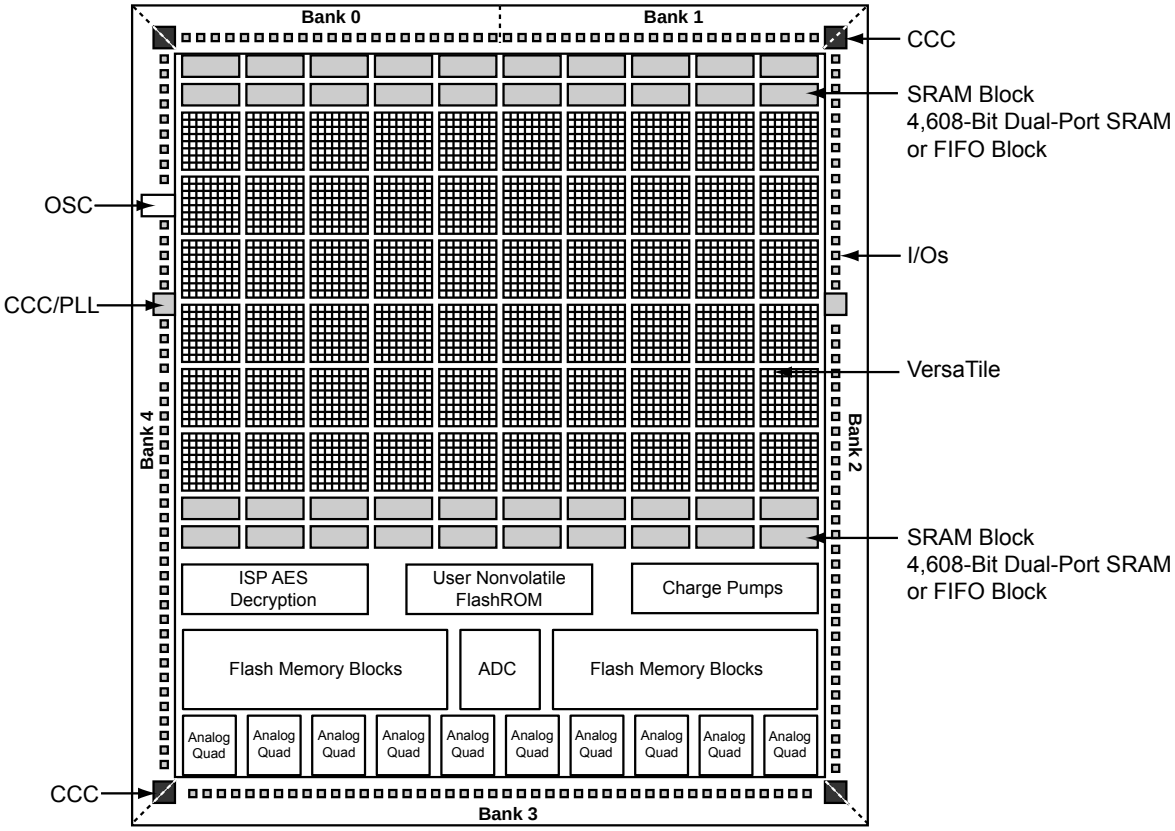


***Figure 11-3* • Block Representation of the AES Decryption Core in a Fusion AFS600 FPGA**

Security Features

IGLOO and ProASIC3 devices have two entities inside: FlashROM and the FPGA core fabric. Fusion devices contain three entities: FlashROM, FBs, and the FPGA core fabric. The parts can be programmed or updated independently with a STAPL programming file. The programming files can be AES-encrypted or plaintext. This allows maximum flexibility in providing security to the entire device. Refer to the "Programming Flash Devices" section on page 221 for information on the FlashROM structure.

Unlike SRAM-based FPGA devices, which require a separate boot PROM to store programming data, low power flash devices are nonvolatile, and the secured configuration data is stored in on-chip flash cells that are part of the FPGA fabric. Once programmed, this data is an inherent part of the FPGA array and does not need to be loaded at system power-up. SRAM-based FPGAs load the configuration bitstream upon power-up; therefore, the configuration is exposed and can be read easily.

The built-in FPGA core, FBs, and FlashROM support programming files encrypted with the 128-bit AES (FIPS-192) block ciphers. The AES key is stored in dedicated, on-chip flash memory and can be programmed before the device is shipped to other parties (allowing secure remote field updates).

Security in ARM-Enabled Low Power Flash Devices

There are slight differences between the regular flash devices and the ARM®-enabled flash devices, which have the M1 and M7 prefix.

The AES key is used by Microsemi and preprogrammed into the device to protect the ARM IP. As a result, the design is encrypted along with the ARM IP, according to the details below.

Security in Action

This section illustrates some applications of the security advantages of Microsemi's devices (Figure 11-6).

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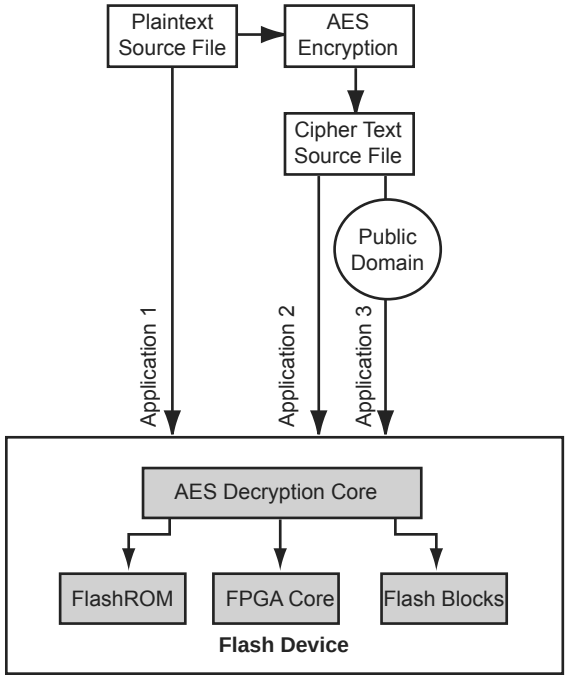

Note: Flash blocks are only used in Fusion devices

***Figure 11-6* • Security Options**

Generating Programming Files

Generation of the Programming File in a Trusted Environment—Application 1

As discussed in the "Application 1: Trusted Environment" section on page 243, in a trusted environment, the user can choose to program the device with plaintext bitstream content. It is possible to use plaintext for programming even when the FlashLock Pass Key option has been selected. In this application, it is not necessary to employ AES encryption protection. For AES encryption settings, refer to the next sections.

The generated programming file will include the security setting (if selected) and the plaintext programming file content for the FPGA array, FlashROM, and/or FBs. These options are indicated in Table 11-2 and Table 11-3.

***Table 11-2* • IGLOO and ProASIC3 Plaintext Security Options, No AES**

Security Protection	FlashROM Only	FPGA Core Only	Both FlashROM and FPGA
No AES / no FlashLock	✓	✓	✓
FlashLock only	✓	✓	✓
AES and FlashLock	–	–	–

***Table 11-3* • Fusion Plaintext Security Options**

Security Protection	FlashROM Only	FPGA Core Only	FB Core Only	All
No AES / no FlashLock	✓	✓	✓	✓
FlashLock	✓	✓	✓	✓
AES and FlashLock	–	–	–	–

Note: For all instructions, the programming of Flash Blocks refers to Fusion only.

For this scenario, generate the programming file as follows:

1. Select the **Silicon features to be programmed** (Security Settings, FPGA Array, FlashROM, Flash Memory Blocks), as shown in Figure 11-10 on page 248 and Figure 11-11 on page 248. Click **Next**.

   If **Security Settings** is selected (i.e., the FlashLock security Pass Key feature), an additional dialog will be displayed to prompt you to select the security level setting. If no security setting is selected, you will be directed to Step 3.

***Table 11-5* • FlashLock Security Options for Fusion**

Security Option	FlashROM Only	FPGA Core Only	FB Core Only	All
No AES / no FlashLock	–	–	–	–
FlashLock	✓	✓	✓	✓
AES and FlashLock	✓	✓	✓	✓

For this scenario, generate the programming file as follows:

1. Select only the **Security settings** option, as indicated in Figure 11-14 and Figure 11-15 on page 252. Click **Next**.

***Figure 11-14* • Programming IGLOO and ProASIC3 Security Settings Only**

Table 11-6 and Table 11-7 show all available options. If you want to implement custom levels, refer to the "Advanced Options" section on page 256 for information on each option and how to set it.

3. When done, click **Finish** to generate the Security Header programming file.

***Table 11-6* • All IGLOO and ProASIC3 Header File Security Options**

Security Option	FlashROM Only	FPGA Core Only	Both FlashROM and FPGA
No AES / no FlashLock	✓	✓	✓
FlashLock only	✓	✓	✓
AES and FlashLock	✓	✓	✓

Note: ✓ = options that may be used

***Table 11-7* • All Fusion Header File Security Options**

Security Option	FlashROM Only	FPGA Core Only	FB Core Only	All
No AES / No FlashLock	✓	✓	✓	✓
FlashLock	✓	✓	✓	✓
AES and FlashLock	✓	✓	✓	✓

Generation of Programming Files with AES Encryption—Application 3

This section discusses how to generate design content programming files needed specifically at unsecured or remote locations to program devices with a Security Header (FlashLock Pass Key and AES key) already programmed ("Application 2: Nontrusted Environment—Unsecured Location" section on page 243 and "Application 3: Nontrusted Environment—Field Updates/Upgrades" section on page 244). In this case, the encrypted programming file must correspond to the AES key already programmed into the device. If AES encryption was previously selected to encrypt the FlashROM, FBs, and FPGA array, AES encryption must be set when generating the programming file for them. AES encryption can be applied to the FlashROM only, the FBs only, the FPGA array only, or all. The user must ensure both the FlashLock Pass Key and the AES key match those already programmed to the device(s), and all security settings must match what was previously programmed. Otherwise, the encryption and/or device unlocking will not be recognized when attempting to program the device with the programming file.

The generated programming file will be AES-encrypted.

In this scenario, generate the programming file as follows:

1. Deselect **Security settings** and select the portion of the device to be programmed (Figure 11-17 on page 254). Select **Programming previously secured device(s**). Click **Next**.

signal deactivated, which also has the effect of disabling the input buffers. The SAMPLE/PRELOAD instruction captures the status of pads in parallel and shifts them out as new data is shifted in for loading into the Boundary Scan Register (BSR). When the device is in an unprogrammed state, the OE and output BSR will be undefined; however, the input BSR will be defined as long as it is connected and being used. For JTAG timing information on setup, hold, and fall times, refer to the *FlashPro User's Guide*.

ISP Support in Flash-Based Devices

The flash FPGAs listed in Table 12-1 support the ISP feature and the functions described in this document.

***Table 12-1* • Flash-Based FPGAs Supporting ISP**

Series	Family*	Description
IGLOO	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology
	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards
	IGLOO nano	The industry's lowest-power, smallest-size solution
	IGLOO PLUS	IGLOO FPGAs with enhanced I/O capabilities
ProASIC3	ProASIC3	Low power, high-performance 1.5 V FPGAs
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications
SmartFusion	SmartFusion	Mixed signal FPGA integrating ProASIC3 FPGA fabric, programmable microcontroller subsystem (MSS) which includes programmable analog and an ARM® Cortex™-M3 hard processor and flash memory in a monolithic device
Fusion	Fusion	Mixed signal FPGA integrating ProASIC3 FPGA fabric, programmable analog block, support for ARM® Cortex™-M1 soft processors, and flash memory into a monolithic device
ProASIC	ProASIC	First generation ProASIC devices
	ProASIC PLUS	Second generation ProASIC devices

*Note: *The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.*

IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 12-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 12-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.

Security in ARM-Enabled Low Power Flash Devices

There are slight differences between the regular flash device and the ARM-enabled flash devices, which have the M1 prefix.

The AES key is used by Microsemi and preprogrammed into the device to protect the ARM IP. As a result, the design will be encrypted along with the ARM IP, according to the details below.

Cortex-M1 and Cortex-M3 Device Security

Cortex-M1–enabled and Cortex-M3 devices are shipped with the following security features:

- FPGA array enabled for AES-encrypted programming and verification
- FlashROM enabled for AES-encrypted write and verify
- Embedded Flash Memory enabled for AES encrypted write

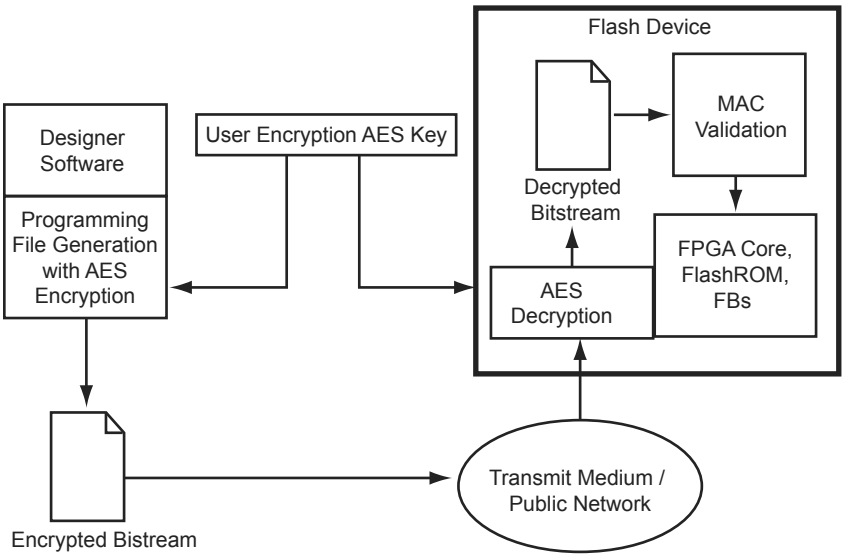

***Figure 12-1* • AES-128 Security Features**

Silicon Testing and Debugging

In many applications, the design needs to be tested, debugged, and verified on real silicon or in the final embedded application. To debug and test the functionality of designs, users may need to monitor some internal logic (or nets) during device operation. The approach of adding design test pins to monitor the critical internal signals has many disadvantages, such as limiting the number of user I/Os. Furthermore, adding external I/Os for test purposes may require additional or dedicated board area for testing and debugging.

The UJTAG tiles of low power flash devices offer a flexible and cost-effective solution for silicon test and debug applications. In this solution, the signals under test are shifted out to the TDO pin of the TAP Controller. The main advantage is that all the test signals are monitored from the TDO pin; no pins or additional board-level resources are required. Figure 16-6 illustrates this technique. Multiple test nets are brought into an internal MUX architecture. The selection of the MUX is done using the contents of the TAP Controller instruction register, where individual instructions (values from 16 to 127) correspond to different signals under test. The selected test signal can be synchronized with the rising or falling edge of TCK (optional) and sent out to UTDO to drive the TDO output of JTAG.

For flash devices, TDO (the output) is configured as low slew and the highest drive strength available in the technology and/or device. Here are some examples:

1. If the device is A3P1000 and VCCI is 3.3 V, TDO will be configured as LVTTL 3.3 V output, 24 mA, low slew.
2. If the device is AGLN020 and VCCI is 1.8 V, TDO will be configured as LVCMOS 1.8 V output, 4 mA, low slew.
3. If the device is AGLE300 and VCCI is 2.5 V, TDO will be configured as LVCMOS 2.5 V output, 24 mA, low slew.

The test and debug procedure is not limited to the example in Figure 16-5 on page 303. Users can customize the debug and test interface to make it appropriate for their applications. For example, multiple test signals can be registered and then sent out through UTDO, each at a different edge of TCK. In other words, *n* signals are sampled with an F_{TCK} / *n* sampling rate. The bandwidth of the information sent out to TDO is always proportional to the frequency of TCK.

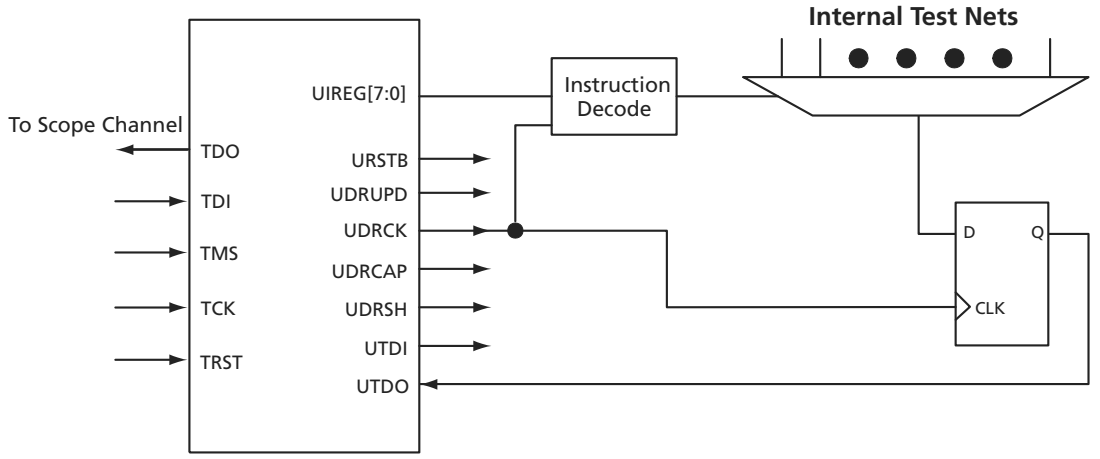

***Figure 16-6* • UJTAG Usage Example in Test and Debug Applications**